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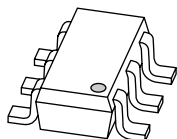
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Kind regards,

Team Nexperia



# PBSS4440D

40 V NPN low  $V_{CEsat}$  (BISS) transistor

Rev. 02 — 11 December 2009

Product data sheet

## 1. Product profile

### 1.1 General description

NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a SOT457 (SC-74) SMD plastic package.

PNP complement: PBSS5440D.

### 1.2 Features

- Ultra low collector-emitter saturation voltage  $V_{CEsat}$
- 4 A continuous collector current capability  $I_C$  (DC)
- Up to 15 A peak current
- Very low collector-emitter saturation resistance
- High efficiency due to less heat generation

### 1.3 Applications

- Power management functions
- Charging circuits
- DC-to-DC conversion
- MOSFET gate driving
- Power switches (e.g. motors, fans)
- Thin Film Transistor (TFT) backlight inverter

### 1.4 Quick reference data

Table 1. Quick reference data

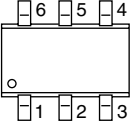
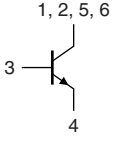
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	40	V
$I_C$	collector current (DC)		[1]	-	4	A
$I_{CM}$	peak collector current	$t = 1$ ms or limited by $T_{j(max)}$	-	-	15	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 6$ A; $I_B = 600$ mA	[2]	55	75	m $\Omega$

[1] Device mounted on a ceramic Printed-Circuit Board (PCB),  $Al_2O_3$ , standard footprint.

[2] Pulse test:  $t_p \leq 300$   $\mu$ s;  $\delta \leq 0.02$ .

## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	collector		 sym014
2	collector		
3	base		
4	emitter		
5	collector		
6	collector		

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4440D	SC-74	plastic surface mounted package; 6 leads	SOT457

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4440D	61

## 5. Limiting values

Table 5. Limiting values

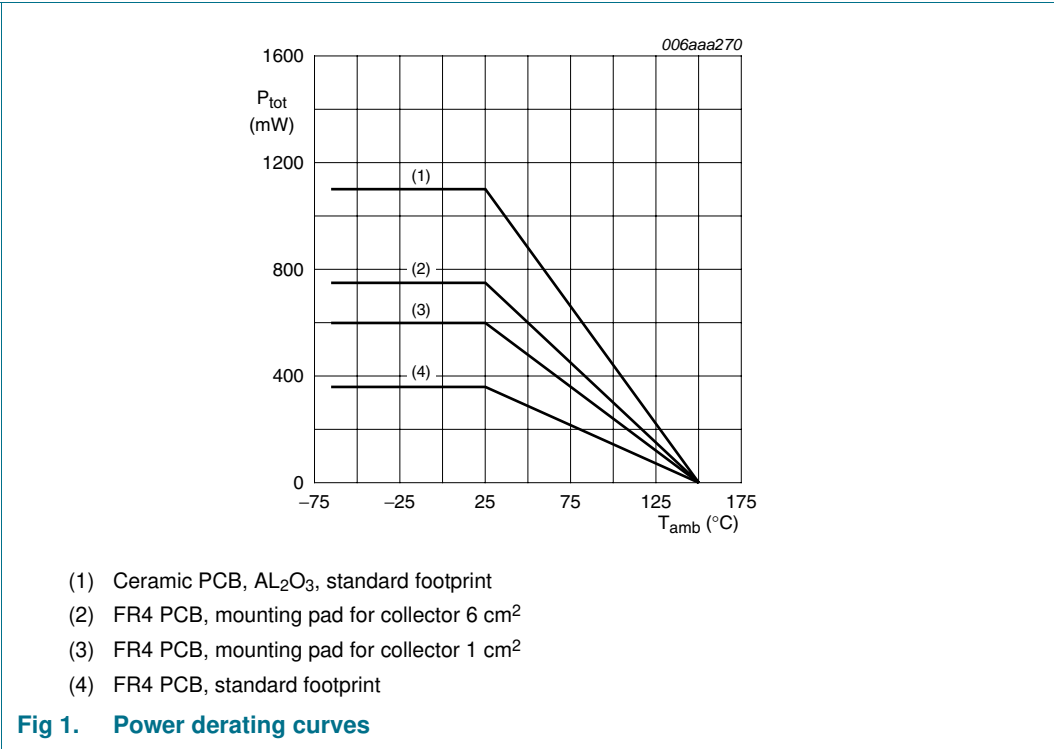
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
I <sub>C</sub>	collector current (DC)		[1] -	4	A
I <sub>CM</sub>	peak collector current	t = 1 ms or limited by T <sub>j(max)</sub>	-	15	A
I <sub>B</sub>	base current (DC)		-	0.8	A
I <sub>BM</sub>	peak base current	t <sub>p</sub> ≤ 300 μs	-	2	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2] -	360	mW
			[3] -	600	mW
			[4] -	750	mW
			[1] -	1.1	W
			[2][5] -	2.5	W

**Table 5. Limiting values ...continued**  
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	junction temperature		-	150	°C
$T_{amb}$	ambient temperature		-65	+150	°C

- [1] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [5] Operated under pulsed conditions: Duty cycle  $\delta \leq 10\%$  and pulse width  $t_p \leq 10$  ms.

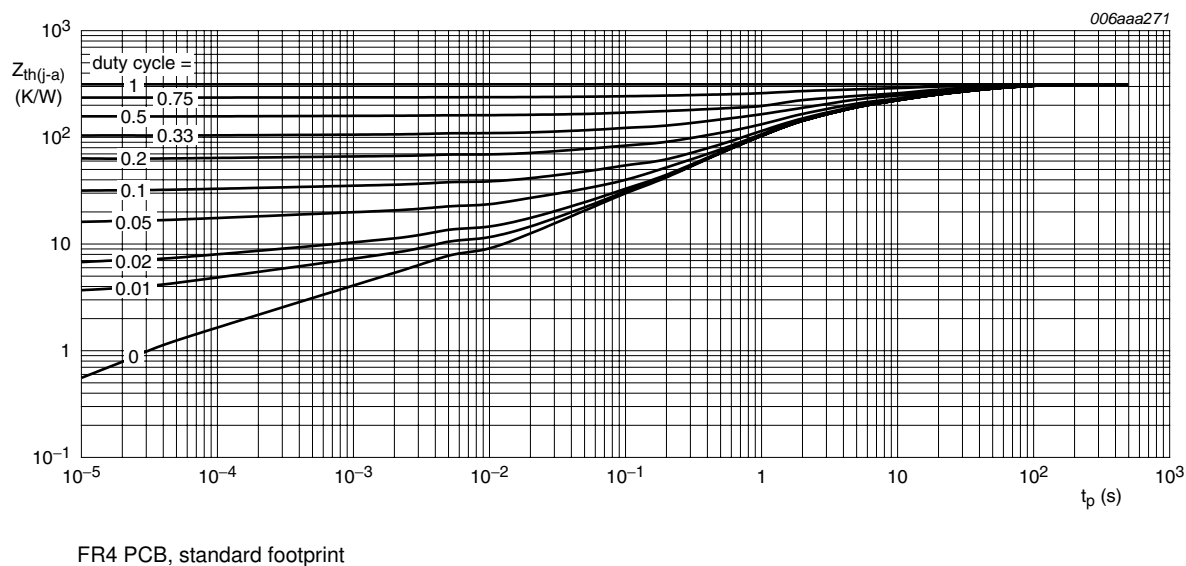


## 6. Thermal characteristics

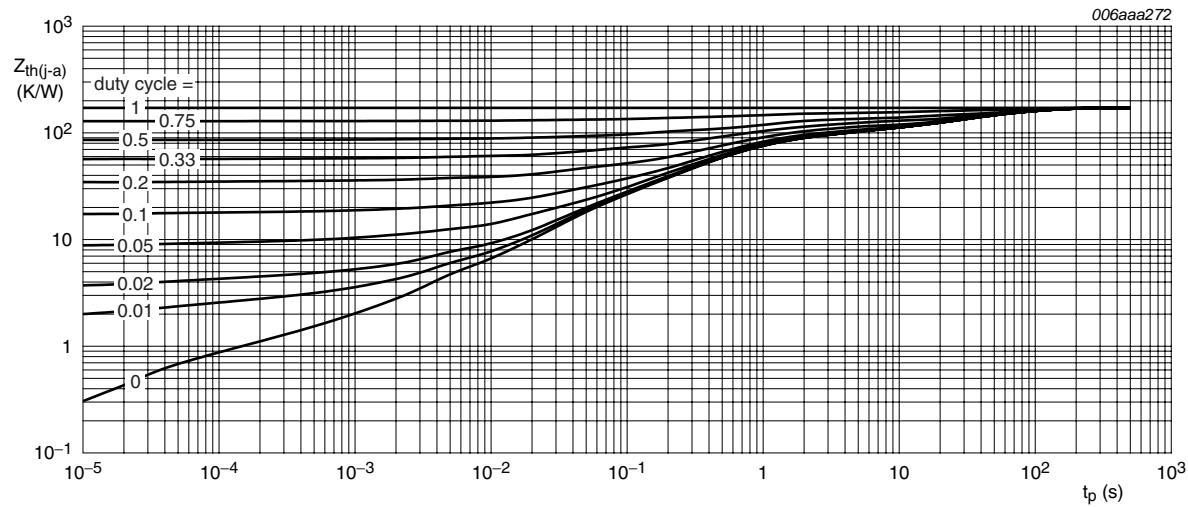
### Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	350	K/W
			[2]	-	-	208	K/W
			[3]	-	-	160	K/W
			[4]	-	-	113	K/W
			[1][5]	-	-	50	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	45	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, AL<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Operated under pulsed conditions: Duty cycle  $\delta \leq 10\%$  and pulse width  $t_p \leq 10$  ms.

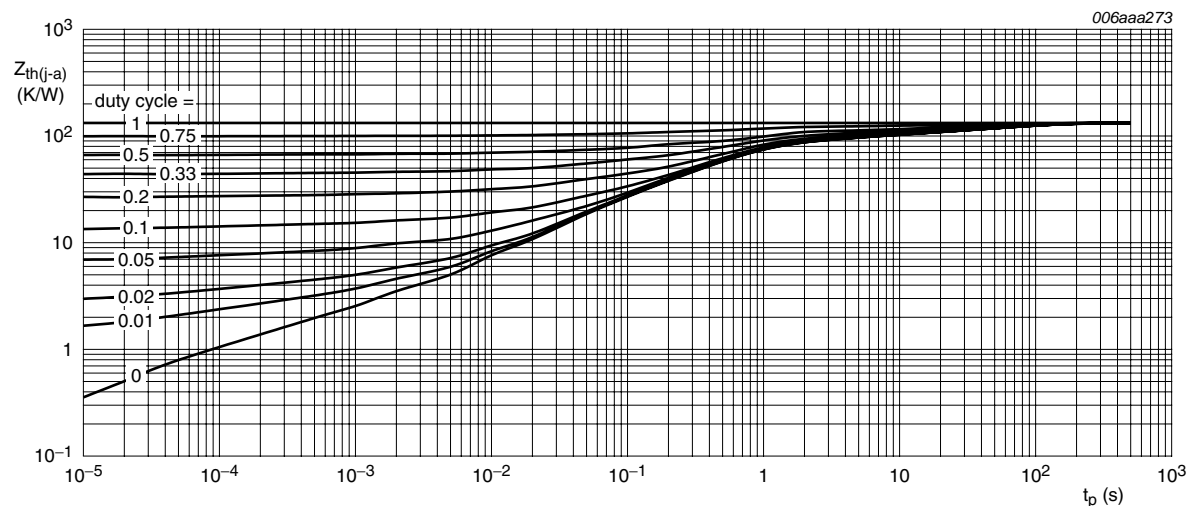


**Fig 2. Transient thermal impedance from junction to ambient as a function of pulse time; typical values**



FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse time; typical values



FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>

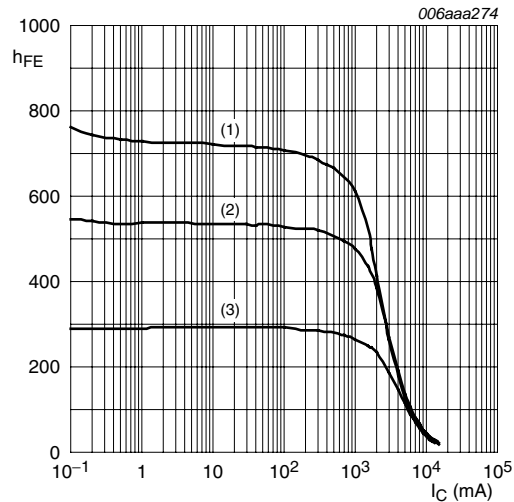
Fig 4. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

## 7. Characteristics

**Table 7. Characteristics**
 $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

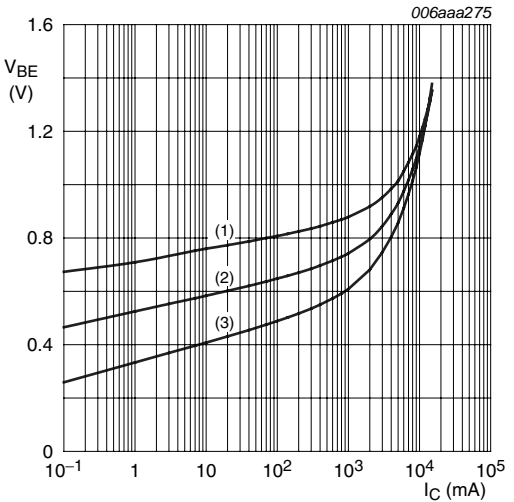
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 40\text{ V}; I_E = 0\text{ A}$	-	-	0.1	$\mu\text{A}$
		$V_{CB} = 40\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	$\mu\text{A}$
$I_{CES}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; V_{BE} = 0\text{ V}$	-	-	0.1	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	0.1	$\mu\text{A}$
$h_{FE}$	DC current gain	$V_{CE} = 2\text{ V}; I_C = 0.5\text{ A}$	300	-	-	
		$V_{CE} = 2\text{ V}; I_C = 1\text{ A}$	[1] 300	-	-	
		$V_{CE} = 2\text{ V}; I_C = 2\text{ A}$	[1] 250	-	-	
		$V_{CE} = 2\text{ V}; I_C = 4\text{ A}$	[1] 100	-	-	
		$V_{CE} = 2\text{ V}; I_C = 6\text{ A}$	[1] 50	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 0.5\text{ A}; I_B = 50\text{ mA}$	-	35	60	mV
		$I_C = 1\text{ A}; I_B = 50\text{ mA}$	-	65	110	mV
		$I_C = 2\text{ A}; I_B = 200\text{ mA}$	-	115	180	mV
		$I_C = 4\text{ A}; I_B = 400\text{ mA}$	[1] -	220	300	mV
		$I_C = 6\text{ A}; I_B = 600\text{ mA}$	[1] -	330	450	mV
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 6\text{ A}; I_B = 600\text{ mA}$	[1] -	55	75	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 0.5\text{ A}; I_B = 50\text{ mA}$	-	0.79	0.85	V
		$I_C = 1\text{ A}; I_B = 50\text{ mA}$	-	0.81	0.9	V
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1] -	0.83	1	V
		$I_C = 4\text{ A}; I_B = 400\text{ mA}$	[1] -	1.0	1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 2\text{ A}$	-	0.79	1.0	V
$t_d$	delay time	$V_{CC} = 10\text{ V}; I_C = 2\text{ A}; I_{Bon} = 0.1\text{ A};$ $I_{Boff} = -0.1\text{ A}$	-	12	-	ns
$t_r$	rise time		-	52	-	ns
$t_{on}$	turn-on time		-	64	-	ns
$t_s$	storage time		-	390	-	ns
$t_f$	fall time		-	120	-	ns
$t_{off}$	turn-off time		-	510	-	ns
$f_T$	transition frequency	$V_{CE} = 10\text{ V}; I_C = 0.1\text{ A};$ $f = 100\text{ MHz}$	-	150	-	MHz
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	30	-	pF

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .



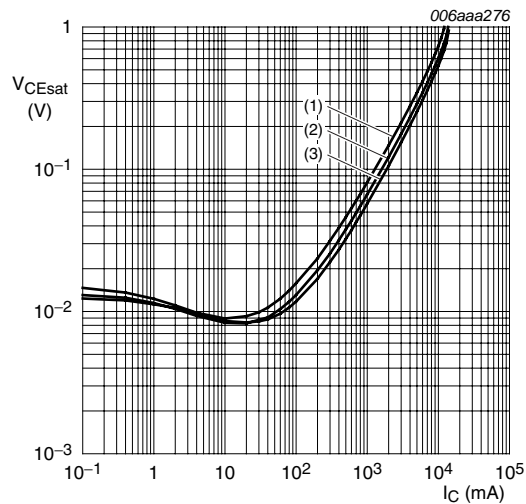
- $V_{CE} = 2\text{ V}$
- (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 5. DC current gain as a function of collector current; typical values



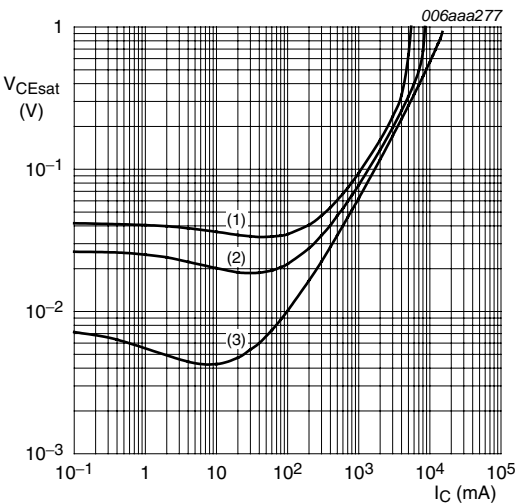
- $V_{CE} = 2\text{ V}$
- (1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 6. Base-emitter voltage as a function of collector current; typical values



- $I_C/I_B = 20$
- (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$
  - (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
  - (3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

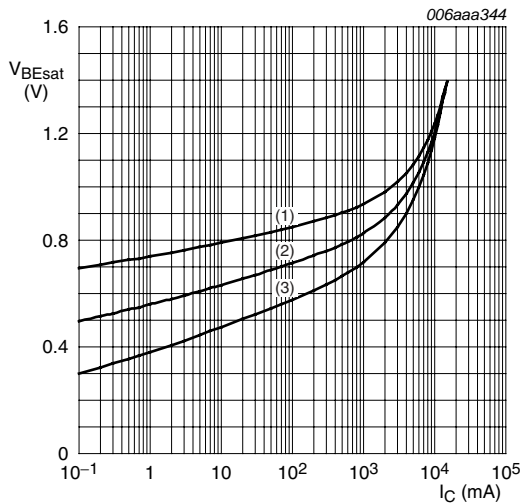
Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



- $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (1)  $I_C/I_B = 100$
  - (2)  $I_C/I_B = 50$
  - (3)  $I_C/I_B = 10$

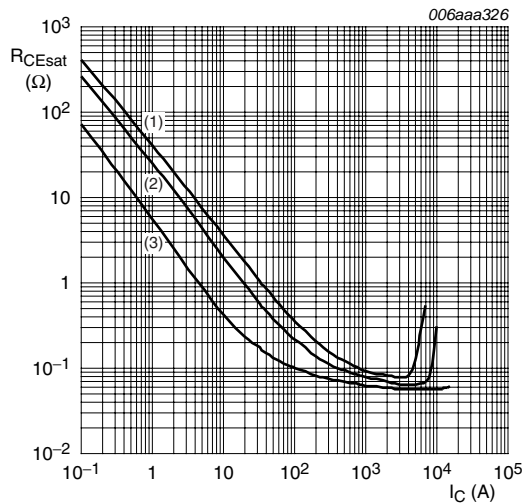
Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values





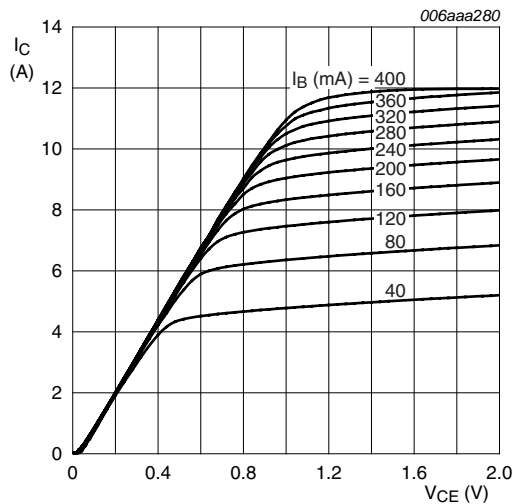
- $I_C/I_B = 20$
- (1)  $T_{amb} = -55^\circ\text{C}$
  - (2)  $T_{amb} = 25^\circ\text{C}$
  - (3)  $T_{amb} = 100^\circ\text{C}$

Fig 9. Base-emitter saturation voltage as a function of collector current; typical values



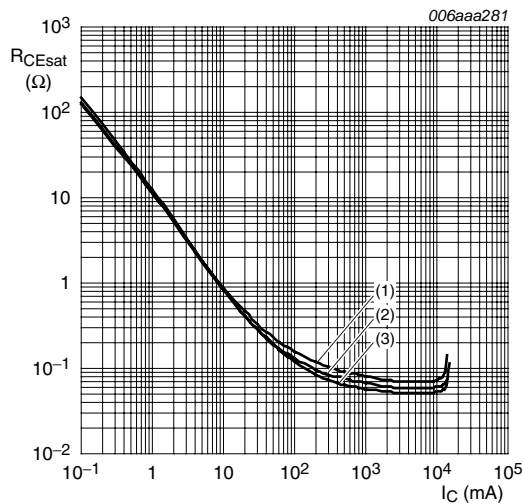
- $T_{amb} = 25^\circ\text{C}$
- (1)  $I_C/I_B = 100$
  - (2)  $I_C/I_B = 50$
  - (3)  $I_C/I_B = 10$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25^\circ\text{C}$

Fig 11. Collector current as a function of collector-emitter voltage; typical values



- $I_C/I_B = 20$
- (1)  $T_{amb} = 100^\circ\text{C}$
  - (2)  $T_{amb} = 25^\circ\text{C}$
  - (3)  $T_{amb} = -55^\circ\text{C}$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

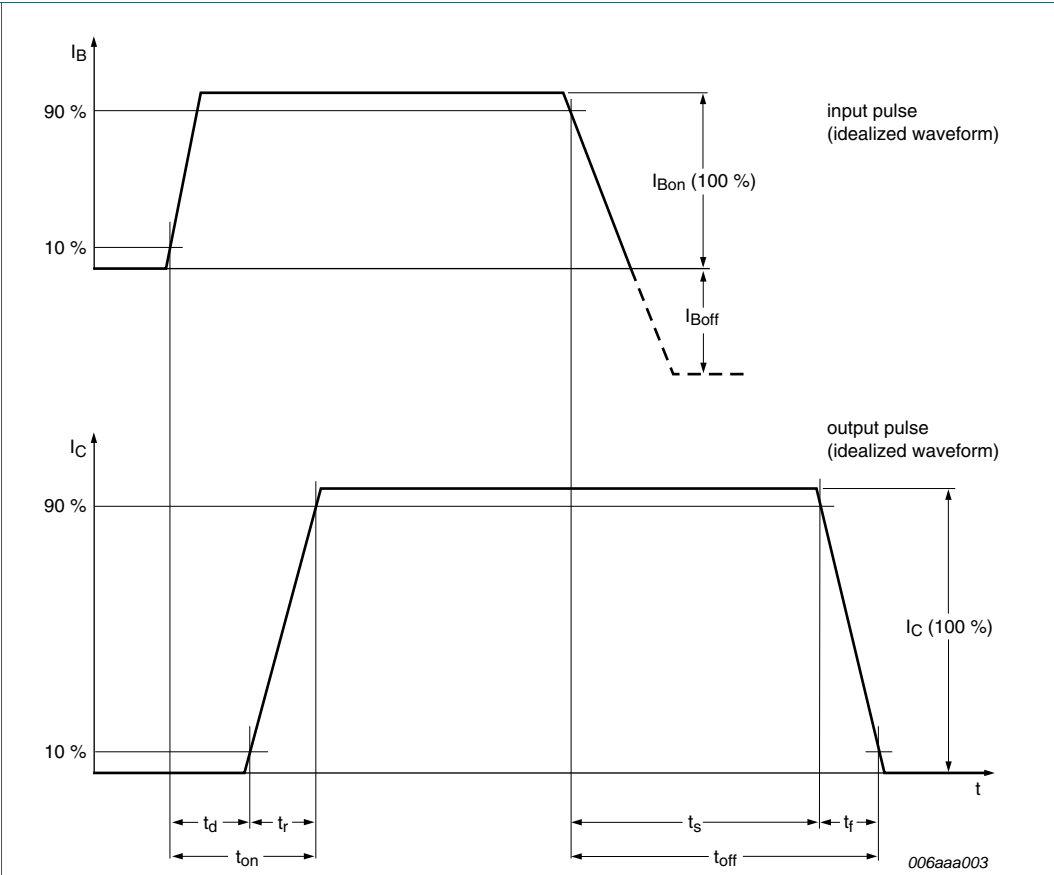
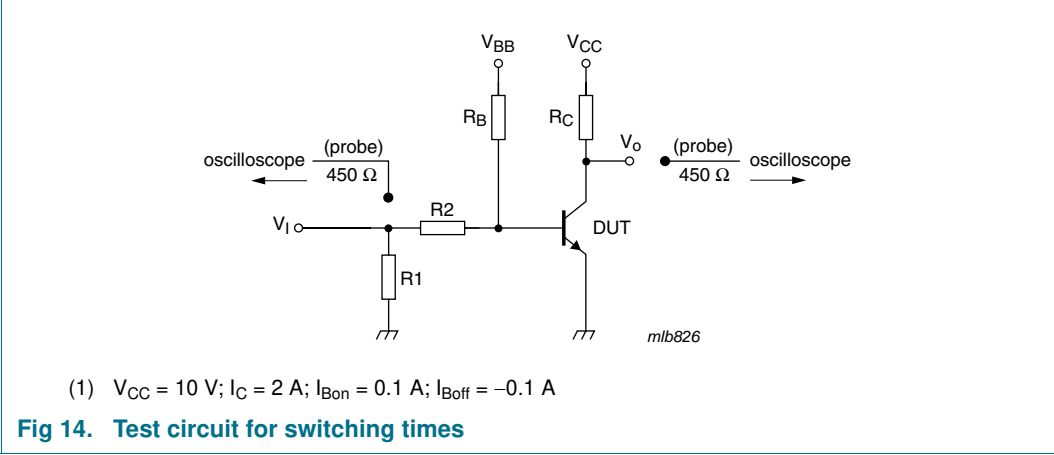
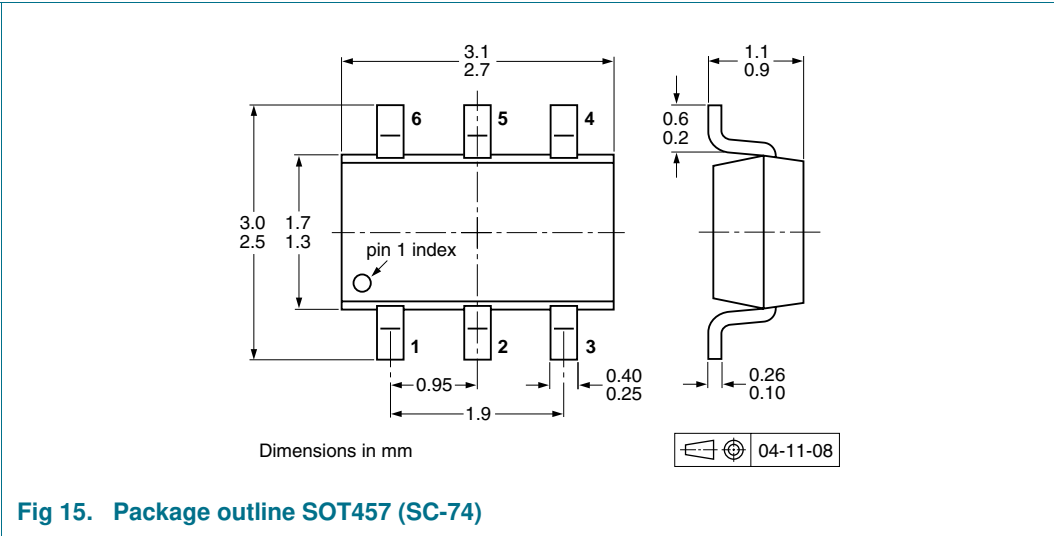


Fig 13. BISS transistor switching time definition



9. Package outline



10. Packing information

**Table 8. Packing methods**  
The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number	Package	Description	Packing quantity		
			3000	5000	10000
PBSS4440D	SOT457	4 mm pitch, 8 mm tape and reel; T1	<sup>[2]</sup> -115	-	-135
		4 mm pitch, 8 mm tape and reel; T2	<sup>[3]</sup> -125	-	-165

[1] For further information and the availability of packing methods, see [Section 13](#).  
[2] T1: normal taping  
[3] T2: reverse taping

## 11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4440D_2	20091211	Product data sheet	-	PBSS4440D_1
Modifications:	<ul style="list-style-type: none"><li>• This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.</li><li>• <a href="#">Figure 2 “Transient thermal impedance from junction to ambient as a function of pulse time; typical values”</a>: updated</li><li>• <a href="#">Figure 3 “Transient thermal impedance from junction to ambient as a function of pulse time; typical values”</a>: updated</li><li>• <a href="#">Figure 4 “Transient thermal impedance from junction to ambient as a function of pulse time; typical values”</a>: updated</li><li>• <a href="#">Figure 11 “Collector current as a function of collector-emitter voltage; typical values”</a>: updated</li></ul>			
PBSS4440D_1	20050421	Product data sheet	-	-

## 12. Legal information

### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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